AUTOMOTIVE

RoHS

COMPLIANT

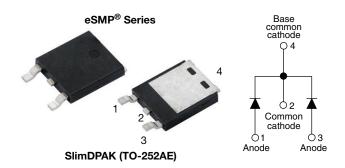
HALOGEN

FREE



Vishay Semiconductors

Hyperfast Rectifier, 2 x 4 A FRED Pt®



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
I _{F(AV)}	2 x 4 A			
V _R	100 V			
V _F at I _F	0.71 V			
t _{rr} (typ.)	16 ns			
T _J max.	175 °C			
Package	SlimDPAK (TO-252AE)			
Circuit configuration	Common cathode			

FEATURES

- · Hyperfast recovery time
- 175 °C max. operating junction temperature
- Low forward voltage drop reduced Q_{rr} and soft recovery
- · Low leakage current
- Very low profile typical height of 1.3 mm
- Polyimide passivation for high reliability standard
- Ideal for automated placement
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyper fast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS inverters or as freewheeling diodes. Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

MECHANICAL DATA

Case: SlimDPAK (TO-252AE)

Molding compound meets UL 94 V-0 flammability rating

Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per

J-STD-002

ABSOLUTE MAXIMUM RATINGS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage		V_{RRM}		100	V
Average rectified forward	per leg		T _C = 167 °C	4	
current	per device	I _{F(AV)}	1 _C = 167 C	8	Α
Non-repetitive peak surge current per leg		I _{FSM}	T _J = 25 °C, 10 ms sine pulse wave	100	
Operating junction and storage temperatures		T _J , T _{Stg}		-55 to +175	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR} , V_{R}	I _R = 100 μA	100	-	-	
		I _F = 4 A	-	0.88	1.0	V
Forward voltage per leg	V _F	I _F = 8 A	-	0.97	1.14	
		I _F = 4 A, T _J = 150 °C	-	0.71	0.80	
		I _F = 8 A, T _J = 150 °C	-	0.8	1.0	
		V _R = V _R rated	-	-	4	
Reverse leakage current per leg	I _R	T _J = 125 °C, V _R = V _R rated	-	-	40	μΑ
		T _J = 150 °C, V _R = V _R rated	-	-	80	
Junction capacitance per leg	C _T	V _R = 100 V	-	17	-	pF



www.vishay.com

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 A, dI_F/dt = 10$	00 A/μs, V _R = 30 V	-	16	-	
Reverse recovery time		I _F = 0.5 A, I _R = 1 A, I _{RR} = 0.25 A		-	-	25	
	t _{rr}	T _J = 25 °C	I _F = 4 A dI _F /dt = 200 A/μs V _R = 160 V	-	20	-	ns
		T _J = 125 °C		-	30	-	
Peak recovery current	I _{RRM}	T _J = 25 °C		-	2.5	-	^
		T _J = 125 °C		-	4	-	- A
Dayaraa raaayary aharga	everse recovery charge Q _{rr}	T _J = 25 °C		-	25	-	nC
neverse recovery charge		T _J = 125 °C		-	60	-	110

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C
Thermal resistance, junction to ambient per diode	R _{thJA} (1)(2)		-	73	90	°C/W
Thermal resistance, junction to mount per diode	R _{thJM} (3)		-	2.1	2.5	°C/W
Marking device		Case style SlimDPAK (TO-252AE)		8CV	H01	-

Notes

- $^{(1)}$ The heat generated must be less than thermal conductivity from junction to ambient; $dP_D/dT_J < 1$ R_{thJA}
- $^{(2)}$ Free air, mounted or recommended copper pad area; thermal resistance R_{thJA} junction to ambient
- (3) Mounted on infinite heatsink

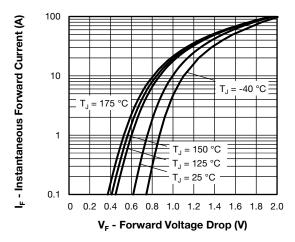


Fig. 1 - Typical Forward Voltage Drop Characteristics

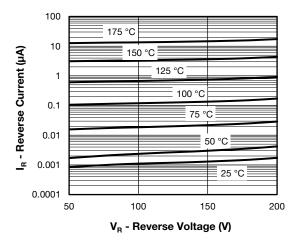


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

Vishay Semiconductors

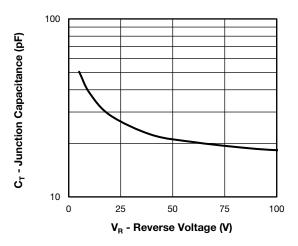


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

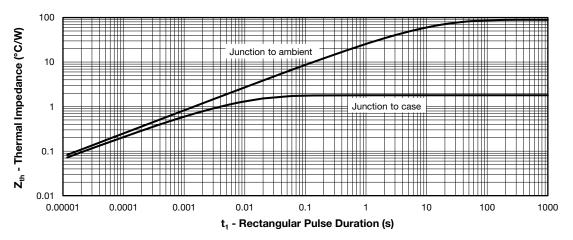


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

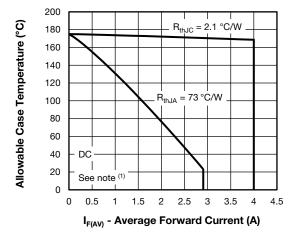


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

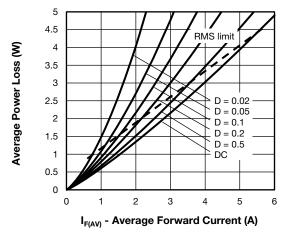


Fig. 6 - Forward Power Loss Characteristics



www.vishay.com

Vishay Semiconductors

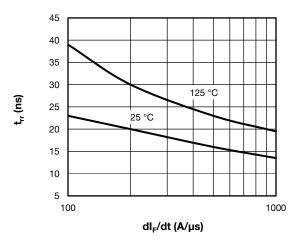


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

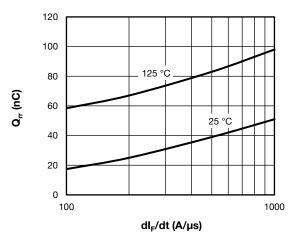
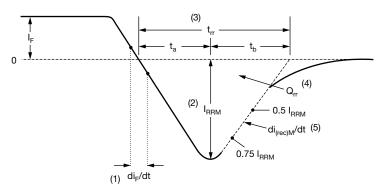


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 6)}; \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{rated } V_R \\ \end{array}$



- di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm l_F$ to point where a line passing through 0.75 $\rm l_{RRM}$ and 0.50 $\rm l_{RRM}$ extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

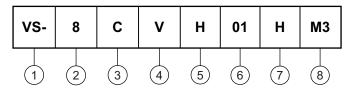
Fig. 9 - Reverse Recovery Waveform and Definitions



Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (8 = 8 A)

3 - Circuit configuration:

C = common cathode

4 - V = SlimDPAK

- Process type,

H = hyperfast recovery

6 - Voltage code (01 = 100 V)

7 - H = AEC-Q101 qualified

8 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-8CVH01HM3/I	4500	4500	13"diameter plastic tape and reel			

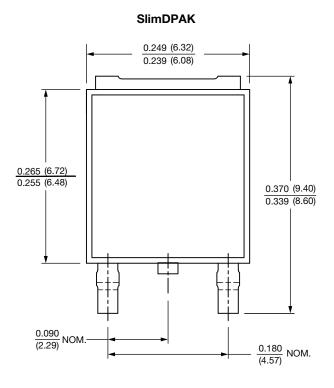
LINKS TO RELATED DOCUMENTS				
Dimensions www.vishay.com/doc?96081				
Part marking information	www.vishay.com/doc?96085			
Packaging information	www.vishay.com/doc?88869			

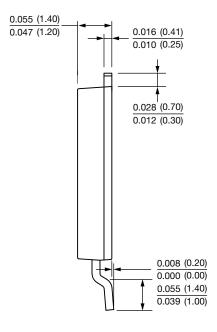


Vishay Semiconductors

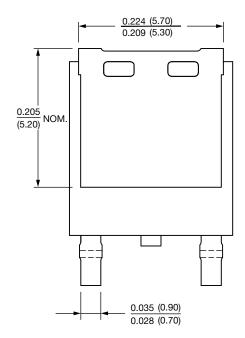
SlimDPAK

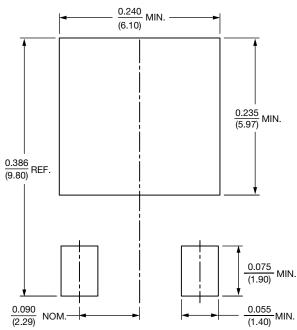
DIMENSIONS in inches (millimeters)





Mounting Pad Layout







Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

单击下面可查看定价,库存,交付和生命周期等信息

>>Vishay(威世)